

isc Silicon PNP Power Transistor

MJD210

DESCRIPTION

- High DC Current Gain–
: $h_{FE} = 70(\text{Min}) @ I_C = -0.5\text{A}$
- Low Collector Saturation Voltage–
: $V_{CE(\text{sat})} = -0.3\text{V}(\text{Max.}) @ I_C = -0.5\text{A}$
- Complement to the NPN MJD200
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

APPLICATIONS

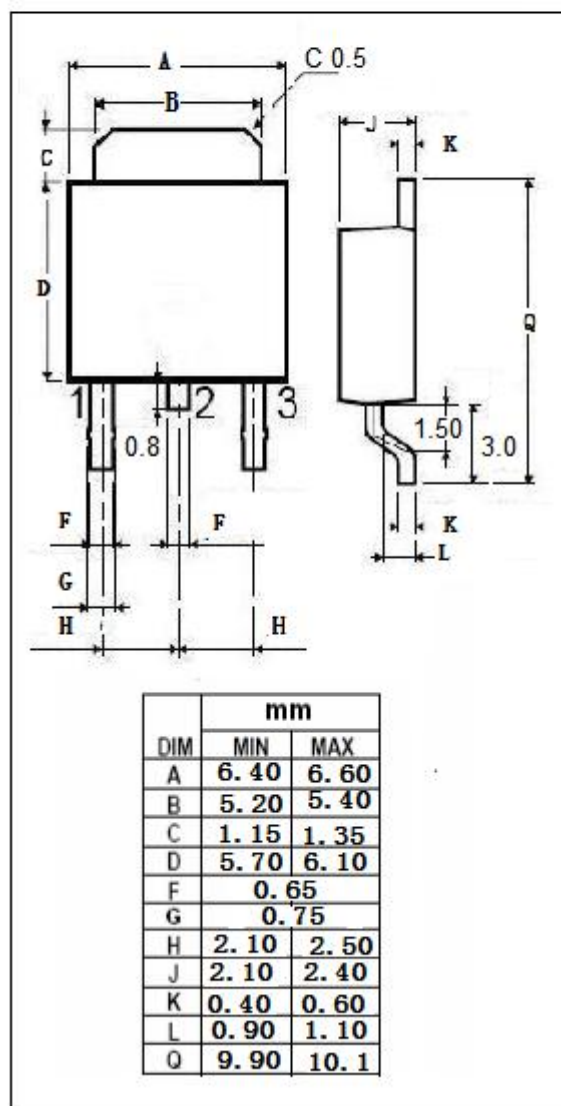
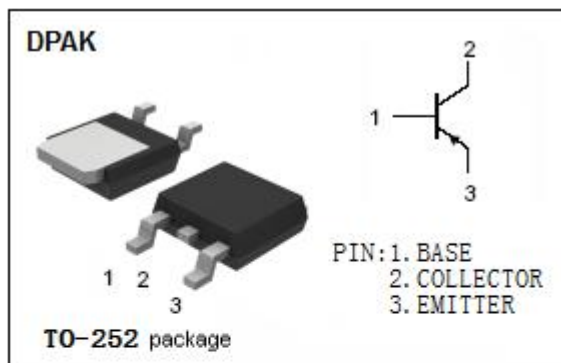
- Designed for low voltage, low -power ,high-gain audio amplifier applications.

ABSOLUTE MAXIMUM RATINGS($T_a=25^\circ\text{C}$)

SYMBOL	PARAMETER	VALUE	UNIT
V_{CBO}	Collector-Base Voltage	-40	V
V_{CEO}	Collector-Emitter Voltage	-25	V
V_{EBO}	Emitter-Base Voltage	-8	V
I_C	Collector Current-Continuous	-5	A
I_{CM}	Collector Current-Peak	-10	A
I_B	Base Current	-1	A
P_C	Collector Power Dissipation $T_a=25^\circ\text{C}$	1.4	W
	Collector Power Dissipation $T_C=25^\circ\text{C}$	12.5	
T_j	Junction Temperature	150	$^\circ\text{C}$
T_{stg}	Storage Temperature Range	-65~150	$^\circ\text{C}$

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	MAX	UNIT
$R_{th\ j-c}$	Thermal Resistance, Junction to Case	10	$^\circ\text{C}/\text{W}$
$R_{th\ j-a}$	Thermal Resistance, Junction to Ambient	89.3	$^\circ\text{C}/\text{W}$



isc Silicon PNP Power Transistor

MJD210

ELECTRICAL CHARACTERISTICS

 $T_C = 25^\circ\text{C}$ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	MAX	UNIT
$V_{CEO(SUS)}$	Collector-Emitter Sustaining Voltage	$I_C = -10\text{mA}; I_B = 0$	-25		V
$V_{CE(sat)-1}$	Collector-Emitter Saturation Voltage	$I_C = -0.5\text{A}; I_B = -50\text{mA}$		-0.3	V
$V_{CE(sat)-2}$	Collector-Emitter Saturation Voltage	$I_C = -2\text{A}; I_B = -0.2\text{A}$		-0.75	V
$V_{CE(sat)-3}$	Collector-Emitter Saturation Voltage	$I_C = -5\text{A}; I_B = -1\text{A}$		-1.8	V
$V_{BE(sat)}$	Base-Emitter Saturation Voltage	$I_C = -5\text{A}; I_B = -1\text{A}$		-2.5	V
$V_{BE(on)}$	Base-Emitter On Voltage	$I_C = -2\text{A}; V_{CE} = -1\text{V}$		-1.6	V
I_{CBO}	Collector Cutoff Current	$V_{CB} = -40\text{V}; I_E = 0$ $V_{CB} = -40\text{V}; I_E = 0; T_C = 125^\circ\text{C}$		-0.1 -0.1	μA mA
I_{EBO}	Emitter Cutoff Current	$V_{EB} = -8\text{V}; I_C = 0$		-0.1	μA
h_{FE-1}	DC Current Gain	$I_C = -0.5\text{A}; V_{CE} = -1\text{V}$	70		
h_{FE-2}	DC Current Gain	$I_C = -2\text{A}; V_{CE} = -1\text{V}$	45	180	
h_{FE-3}	DC Current Gain	$I_C = -5\text{A}; V_{CE} = -2\text{V}$	10		
f_T	Current-Gain—Bandwidth Product	$I_C = -0.1\text{A}; V_{CE} = -10\text{V}; f_{test} = 10\text{MHz}$	65		MHz
C_{OB}	Collector Capacitance	$I_E = 0; V_{CB} = -10\text{V}; f_{test} = 0.1\text{MHz}$	60		pF

Notice:

ISC reserves the rights to make changes of the content herein the datasheet at any time without notification. The information contained herein is presented only as a guide for the applications of our products.

ISC products are intended for usage in general electronic equipment. The products are not designed for use in equipment which require specialized quality and/or reliability, or in equipment

which could have applications in hazardous environments, aerospace industry, or medical field. Please contact us if you intend our products to be used in these special applications.

ISC makes no warranty or guarantee regarding the suitability of its products for any particular purpose, nor does ISC assume any liability arising from the application or use of any products, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages.